



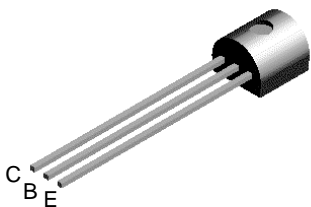
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S9018

**NPN Silicon
Transistors**

Features

- TO-92 Plastic-Encapsulate Transistors
- Capable of 0.31Watts($T_{amb}=25^{\circ}C$) of Power Dissipation.
- Collector-current 0.05A
- Collector-base Voltage 25V
- Operating and storage junction temperature range: $-55^{\circ}C$ to $+150^{\circ}C$
- Marking Code: S9018



Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=100\mu A, I_E=0$)	25	---	Vdc
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=0.1mA, I_B=0$)	18	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_E=100\mu A, I_C=0$)	4.0	---	Vdc
I_{CBO}	Collector Cutoff Current ($V_{CB}=20Vdc, I_E=0$)	---	0.1	μA
I_{CEO}	Collector Cutoff Current ($V_{CE}=15Vdc, I_B=0$)	---	0.1	μA
I_{EBO}	Emitter Cutoff Current ($V_{EB}=3.0Vdc, I_C=0$)	---	0.1	μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain ($I_C=1.0mA, V_{CE}=5.0Vdc$)	28	270	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=10mA, I_B=1.0mA$)	---	0.5	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C=10mA, I_B=1.0mA$)	---	1.4	Vdc

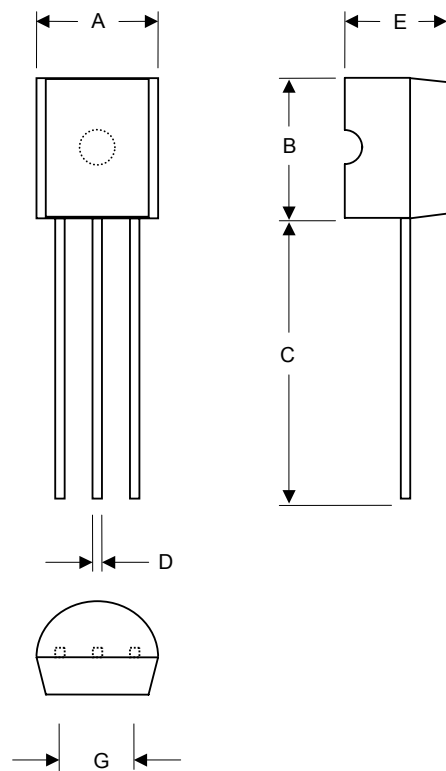
SMALL-SIGNAL CHARACTERISTICS

f_T	Transistor Frequency ($I_C=5.0mA, V_{CE}=5.0Vdc, f=400MHz$)	600	---	MHz
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CLASSIFICATION OF h_{FE}

Rank	G	H	I
Range	70-108	97-146	130-200

TO-92



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.170	.190	4.33	4.83	
B	.170	.190	4.30	4.83	
C	.550	.590	13.97	14.97	
D	.010	.020	0.36	0.56	
E	.130	.160	3.30	3.96	
G	.010	.104	2.44	2.64	